

$I_{F(AV)} = 1.0 \text{ Amp}$   
 $V_R = 30V$

**Major Ratings and Characteristics**

Characteristics	Value	Units
$I_{F(AV)}$ Rectangular waveform	1.0	A
$V_{RRM}$	30	V
$I_{FSM}$ @ $t_p = 5 \text{ ms}$ sine	360	A
$V_F$ @ $1.0 \text{ Apk}$ , $T_J = 125^\circ\text{C}$	0.30	V
$T_J$ range	- 55 to 150	$^\circ\text{C}$

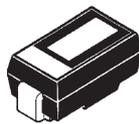
**Description/ Features**

The STPS1L30UPbF surface-mount Schottky rectifier has been designed for applications requiring low forward drop and small foot prints on PC boards. Typical applications are in disk drives, switching power supplies, converters, free-wheeling diodes, battery charging, and reverse battery protection.

- Small foot print, surface mountable
- Very low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Lead-Free ("PbF" suffix)

**Case Styles**

STPS1L30UPbF



SMB



## Voltage Ratings

Part number	STPS1L30UTRPbF
$V_R$ Max. DC Reverse Voltage (V)	30
$V_{RWM}$ Max. Working Peak Reverse Voltage (V)	

## Absolute Maximum Ratings

Parameters	Value	Units	Conditions
$I_{F(AV)}$ Max. Average Forward Current	1.0	A	50% duty cycle @ $T_L = 106^\circ\text{C}$ , rectangular wave form
$I_{FSM}$ Max. Peak One Cycle Non-Repetitive Surge Current	360	A	5 $\mu\text{s}$ Sine or 3 $\mu\text{s}$ Rect. pulse
	75		10ms Sine or 6ms Rect. pulse
$E_{AS}$ Non-Repetitive Avalanche Energy	3.0	mJ	$T_J = 25^\circ\text{C}$ , $I_{AS} = 1\text{A}$ , $L = 6\text{mH}$
$I_{AR}$ Repetitive Avalanche Current	1.0	A	Current decaying linearly to zero in 1 $\mu\text{sec}$ Frequency limited by $T_J$ max. $V_a = 1.5 \times V_r$ typical

## Electrical Specifications

Parameters	Value	Units	Conditions
$V_{FM}$ Max. Forward Voltage Drop (1)	0.420	V	@ 1A
	0.470	V	@ 2A
	0.300	V	@ 1A
	0.375	V	@ 2A
$I_{RM}$ Max. Reverse Leakage Current (1)	0.2	mA	$T_J = 25^\circ\text{C}$
	5.0	mA	$T_J = 100^\circ\text{C}$
	15	mA	$T_J = 125^\circ\text{C}$
$C_T$ Max. Junction Capacitance	200	pF	$V_R = 5V_{DC}$ , (test signal range 100KHz to 1Mhz) $25^\circ\text{C}$
$L_S$ Typical Series Inductance	2.0	nH	Measured lead to lead 5mm from package body
$dv/dt$ Max. Voltage Rate of Change (Rated $V_R$ )	10000	V/ $\mu\text{s}$	

(1) Pulse Width < 300 $\mu\text{s}$ , Duty Cycle < 2%

## Thermal-Mechanical Specifications

Parameters	Value	Units	Conditions
$T_J$ Max. Junction Temperature Range (*)	-55 to 150	$^\circ\text{C}$	
$T_{stg}$ Max. Storage Temperature Range	-55 to 150	$^\circ\text{C}$	
$R_{thJL}$ Max. Thermal Resistance Junction to Lead (**)	25	$^\circ\text{C}/\text{W}$	DC operation
$R_{thJA}$ Max. Thermal Resistance Junction to Ambient	80	$^\circ\text{C}/\text{W}$	DC operation
wt Approximate Weight	0.10(0.003)	g (oz.)	
Case Style	SMB		Similar to DO-214AA
Device Marking	IR13L		

(\*)  $\frac{dP_{tot}}{dT_J} < \frac{1}{R_{th(j-a)}}$  thermal runaway condition for a diode on its own heatsink

(\*\*) Mounted 1 inch square PCB

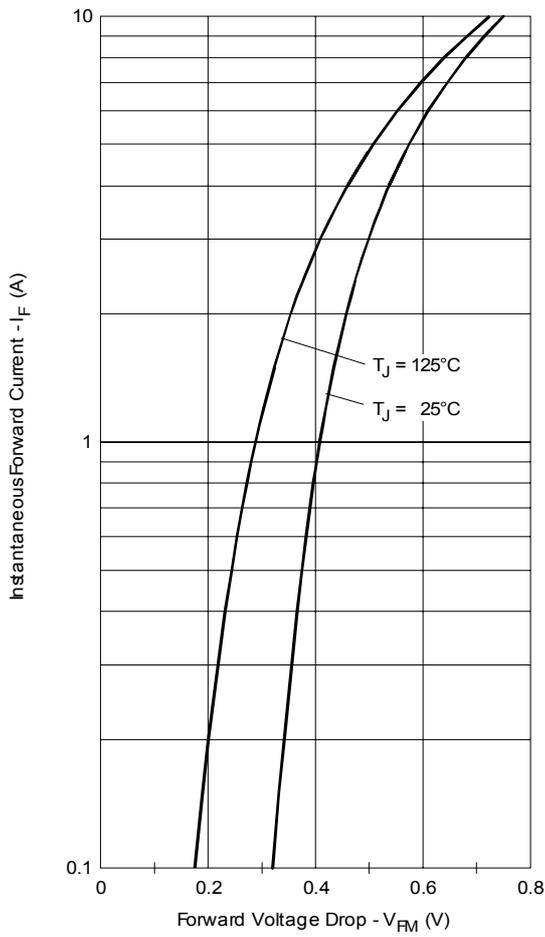


Fig. 1 - Maximum Forward Voltage Drop Characteristics

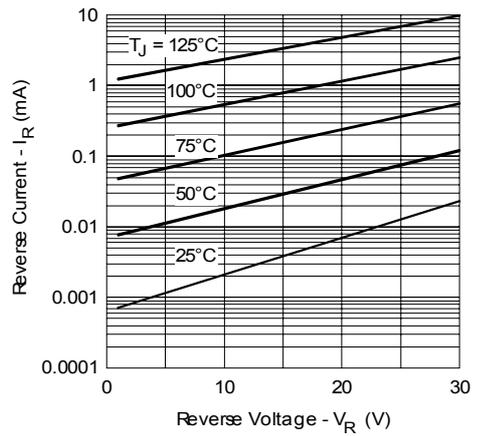


Fig. 2 - Typical Peak Reverse Current Vs. Reverse Voltage

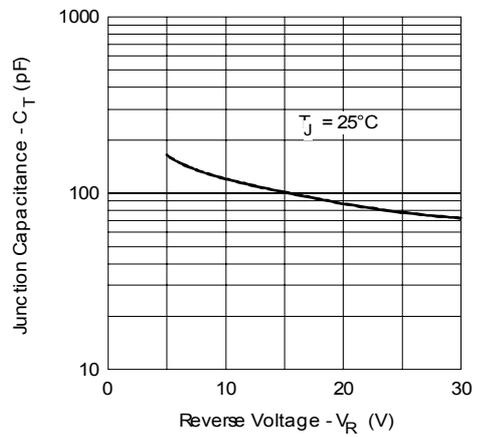


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage

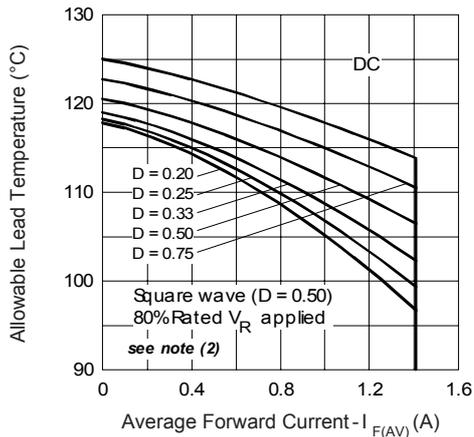


Fig. 4 - Maximum Average Forward Current Vs. Allowable Lead Temperature

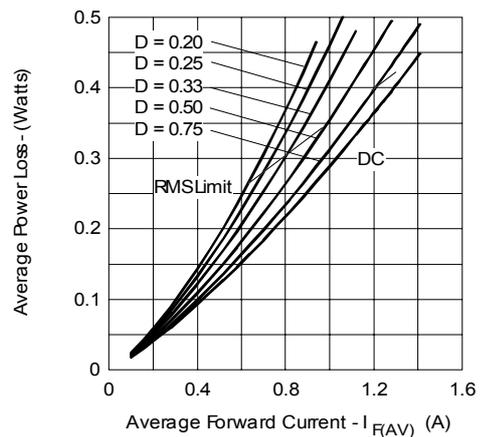


Fig. 5 - Maximum Average Forward Dissipation Vs. Average Forward Current

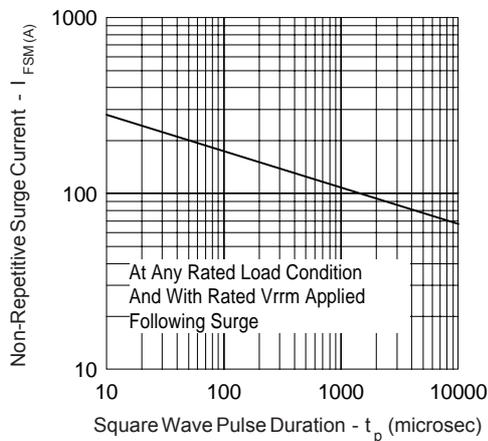


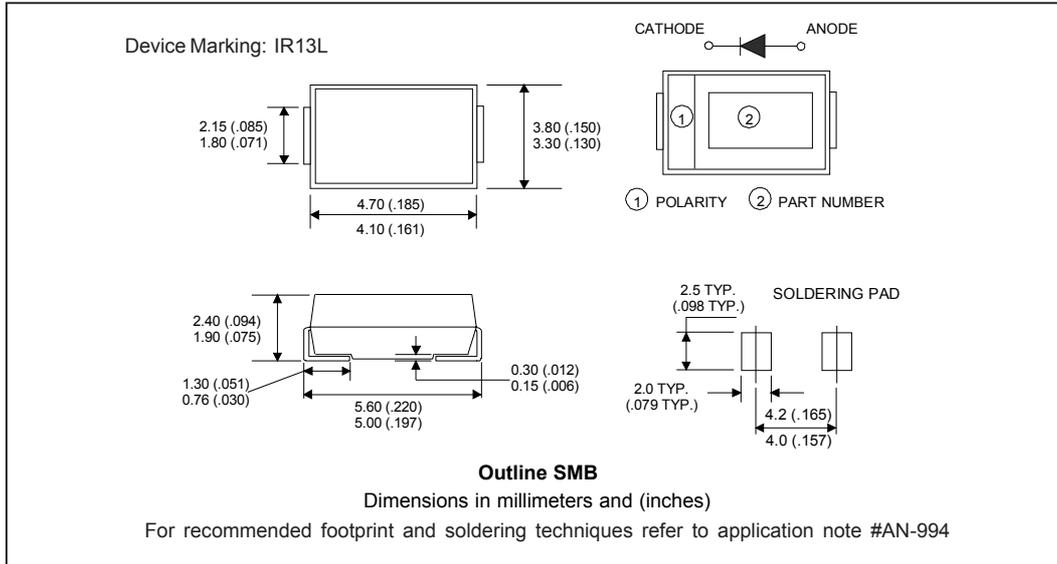
Fig. 6 - Maximum Peak Surge Forward Current Vs. Pulse Duration

(2) Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

$Pd$  = Forward Power Loss =  $I_{F(AV)} \times V_{FM} @ (I_{F(AV)} / D)$  (see Fig. 6);

$Pd_{REV}$  = Inverse Power Loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R @ V_{R1} = 80\%$  rated  $V_R$

Outline Table



Marking & Identification

